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Substitute for form 1449A/PTO INFORMATION DISCLOSURE May 9, 2001 Filing Date STATEMENT BY APPLICANT Theodore H. Fedynyshyn First Named Inventor Group Art Unit 1752 (use as many sheets as necessary) Not Yet Assigned Examiner Name 2 Attorney Docket Number 101328-0151 2 of Sheet

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Applicatio	n Number	09/851,952-4043
Filing Date	,	May 9, 2001
First Name	ed Inventor	Theodore H. Fedynyshyn
Group Art	Jnit	1752
Examiner I	Name	Not Yet Assigned A. Wayee
Attorney D	ocket Number	101328-0151

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